

	<h2>SIR412DP-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIR412DP-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 25V 20A PPAK SO-8</p> <p>Datenblätter:  SIR412DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 819423 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIR412DP-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 25V 20A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	819423 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	3.9W (Ta), 15.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	25V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	20A (Tc)
Rds On (Max) @ Id, Vgs	12 mOhm @ 10A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	16nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	600pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Original-Reel®


















































SIR412DP-T1-GE3 ist neu im Original, Suche SIR412DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIR412DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SIR412DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 SIR416DP VISHAY SIR416DP VISHAY	 SIR412DP-T1-E3 Vishay Precision Group SIR412DP-T1-E3 VISHAY	 SIR410DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 35A PPAK SO-8	 SIR412DP Vishay Precision Group SIR412DP VISHAY
 SIR412DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 25V 20A PPAK SO-8	 SIR414DP VB SIR414DP VB	 SIR414DP-T1-E3 VISHAY SIR414DP-T1-E3 VISHAY	 SIR414DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 50A PPAK SO-8

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Mehr

 SIR172DP-T1-GE3	 SIR172DP-T1-GE3	 SIR330DP-T1-GE3	 SIR330DP-T1-GE3	 SIR402DP-T1-GE3
 SIR402DP-T1-GE3	 SIR403EDP-T1-GE3	 SIR403EDP-T1-GE3	 SIR404DP	 SIR404DP-T1-E3
 SIR404DP-T1-GE3	 SIR404DP-T1-GE3	 SIR406DP	 SIR406DP-T1-E3	 SIR406DP-T1-GE3
 SIR406DP-T1-GE3	 SIR406DP-T1-GE3-S	 SIR408DP-T1-GE3	 SIR408DP-T1-GE3	 SIR410DP-T1-E3
 SIR410DP-T1-GE3	 SIR410DP-T1-GE3	 SIR412DP	 SIR412DP-T1-E3	 SIR412DP-T1-GE3
 SIR414DP	 SIR414DP-T1-GE3	 SIR414DP-T1-GE3	 SIR416DP	 SIR416DP-T1-E3
 SIR416DP-T1-GE3	 SIR416DP-T1-GE3	 SIR418DP-T1-E3	 SIR418DP-T1-GE3	 SIR418DP-T1-GE3
 SIR422DP-T1-E3	 SIR422DP-T1-GE3	 SIR422DP-T1-GE3	 SIR424DP-T1-GE3	 SIR424DP-T1-GE3
 SIR426DP-T1-GE3	 SIR426DP-T1-GE3	 SIR428DP	 SIR428DP-T1-E3	 SIR428DP-T1-GE3
 SIR432DP-T1-GE3	 SIR432DP-T1-GE3	 SIR436DP-T1-E3	 SIR436DP-T1-GE3	 SIR436DP-T1-GE3

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